# SENSITRON SEMICONDUCTOR

### TECHNICAL DATA DATA SHEET 4340, REV. -

# LOW R<sub>DS</sub> HERMETIC POWER MOSFET - N-CHANNEL

### FEATURES:

- 60 Volt, 0.008 Ohm, 110A MOSFET for Glidcop version
- Isolated Hermetic Metal Package
- Ultra Low R<sub>DS (on)</sub>
- Available with Ceramic Seals and Glidcop leads, use part number SHDCG225715

# **MAXIMUM RATINGS** ALL RATINGS ARE AT $T_c = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED.

	U U				
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V <sub>GS</sub>	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I <sub>D25</sub>	-	-	55*	Amps
PULSED DRAIN CURRENT	I <sub>DM</sub>	-	-	440	Amps
OPERATING AND STORAGE TEMPERATURE	T <sub>J</sub> /T <sub>STG</sub>	-55	-	+175	°C
TOTAL DEVICE DISSIPATION	PD	-	-	215	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{ ext{ heta}JC}$	-	-	0.7	°C/W

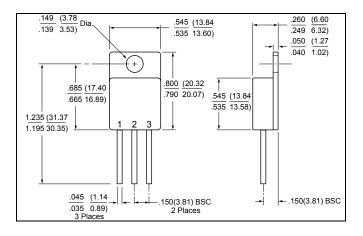
Note: \* current limited by package; die rating is 110A

## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC		SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTA	GE	BV <sub>DSS</sub>	60	-	-	Volts
$V_{GS} = 0$	/, I <sub>D</sub> = 250μA					
STATIC DRAIN TO SOURCE ON STATE RE		R <sub>DS(ON)</sub>				Ω
V <sub>GS</sub> = 10'	V, I <sub>D</sub> = 30A	Glidcop	-	0.006	0.008	
		Version				
STATIC DRAIN TO SOURCE ON STATE RE		R <sub>DS(ON)</sub>				Ω
V <sub>GS</sub> = 10	√, I <sub>D</sub> = 30A	Standard	-	0.008	0.010	
		Version			0	\ / - It -
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$	, I <sub>D</sub> = 250μΑ	$V_{GS(th)}$	1	-	3	Volts
FORWARD TRANSCONDUCTANCE	(   _ 20 A	<b>g</b> <sub>fs</sub>	30	-	-	S(1/Ω)
	/, I <sub>D</sub> = 30A					
	$T = 25^{\circ}C$				1	
$V_{DS}$ = 0.8 x Max. rating, $V_{GS}$ = 0	v, 1j = 25°C Tj = 125°C	IDSS	-	-	50	μA
GATE TO SOURCE LEAKAGE FORWARD	$V_{GS} = 20V$	I <sub>GSS</sub>	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE	$V_{GS} = 20V$ $V_{GS} = -20V$	IGSS	_	_	-100	
TURN ON DELAY TIME	$V_{DD} = 30V$	t <sub>d(ON)</sub>	-	20	30	
RISE TIME	$I_{\rm D} = 55A$			135	200	nsec
TURN OFF DELAY TIME	)/ <b>–</b> 10)/					
	V <sub>GS</sub> =10V	t <sub>d(OFF)</sub>		80	120	
FALL TIME	$R_G = 2.5\Omega$	t <sub>f</sub>		150	220	
	0A, V <sub>GS</sub> = 0V	$V_{SD}$	-	1.1	1.3	Volts
Pulse test, t $\leq$ 300 $\mu$ s, duty c	cycle d $\leq$ 2 %					
REVERSE RECOVERY TIME	T <sub>J</sub> = 25°C,					
	A, V <sub>R</sub> = 100V	t <sub>rr</sub>	-	75	120	nsec
	= 100A/µsec					
REVERSE RECOVERY CHARGE	T <sub>J</sub> = 25°C,					-
	A, V <sub>R</sub> = 100V	Q <sub>rr</sub>	-	0.1	0.25	μC
	= 100A/µsec					
INPUT CAPACITANCE	$V_{GS} = 0 V,$	C <sub>iss</sub>	-	7500	-	_
	$V_{DS} = 25 V$ ,	Coss		1050		pF
REVERSE TRANSFER CAPACITANCE	f = 1.0MHz	C <sub>rss</sub>		700		

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#### **MECHANICAL DIMENSIONS:** in Inches / mm

TO-254

DEVICE TYPE	PIN-1	PIN-2	PIN-3
N-CHANNEL MOSFET TO-254 PACKAGE	DRAIN	SOURCE	GATE

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